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File View Edit Tools Window Help

- L28: (4094) TMR
- L29: (4652) non adj magnetic adj layer$1
- L30: (291) 28 and 29
- L31: (141) double adj tunnel$5
- L32: (49) 31 and TMR
- L33: (19) 32 and 29
- L34: (22) 31 and 29
- L35: (178) 30 and memory
- L36: (88) 35 and stack$6
- L37: (0) multiple adj layer$1 adj TMR
- L38: (7) multilayer adj TMR
- L39: (32500) parallelogram$2
- L40: (7569) magnetic adj memory
- L41: (410) 40 and resistive and cell$1
- L42: (410) 41 and memory
- L43: (275725) 257/$.ccls.
- L44: (60938) 365/$.ccls.
- L45: (151434) 438/$.ccls.
- L46: (74) 42 and 43
- L47: (30) 39 and 40
- L48: (7) magnetic adj fixing adj layer
- L49: (1964) fixing adj layer
- L50: (332) 49 and magnetic
- L51: (52) 50 and 29
- L52: (1) stacked adj fixing adj layer
- L53: (1964) fixing adj layer
- L54: (25) non-magnetic adj sub-layer
- L55: (35) non adj magnetic adj sub adj layer
- L56: (4245) non adj magnetic adj layer
- L57: (50) 53 and 56

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- (0) AND adj logic

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DBs USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

Default operator: OR

Plurals

Highlight all hit terms initially

53 and 56

5/24/04

IFW Term ISR Term Image Text HTML

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval Cla	Inventor	S	C	P	T	3	Image I
1	☐	☐	US 20040065906 A1	20040408	27	Semiconductor integrated circuit device	257/208			Asao, Yoshiaki	☑	☐	☐	☐	☐	US 2004
2	☑	☐	US 20040061978 A1	20040401	20	Differential detection read sensor, thin film head for perpendicular magnetic	360/314	360/324.2		Kawato, Yoshiaki	☐	☐	☐	☐	☐	US 2004
3	☑	☐	US 20030193762 A1	20031016	80	Magneto-resistance effect element, magneto-resistance effect head, magn	360/324.12	360/314		Hayashi, Kazuhiko et al.	☐	☐	☐	☐	☐	US 2003
4	☑	☐	US 20030058576 A1	20030327	30	Magnetic head having an antistripping layer for preventing a magnetic layer f	360/126			Honjo, Hiroaki et al.	☐	☐	☐	☐	☐	US 2003
5	☑	☐	US 20030048581 A1	20030313	19	Thin film magnetic head and a method of producing the same	360/126			Ohtomo, Shigekazu et al.	☐	☐	☐	☐	☐	US 2003
6	–	–	US 20030031897	20030213	18	Magnetic recording medium and	428/694TM	428/65.3;		Fukazawa, Toshio et al.	–	–	–	–	–	US 2003

Hits Details HTML

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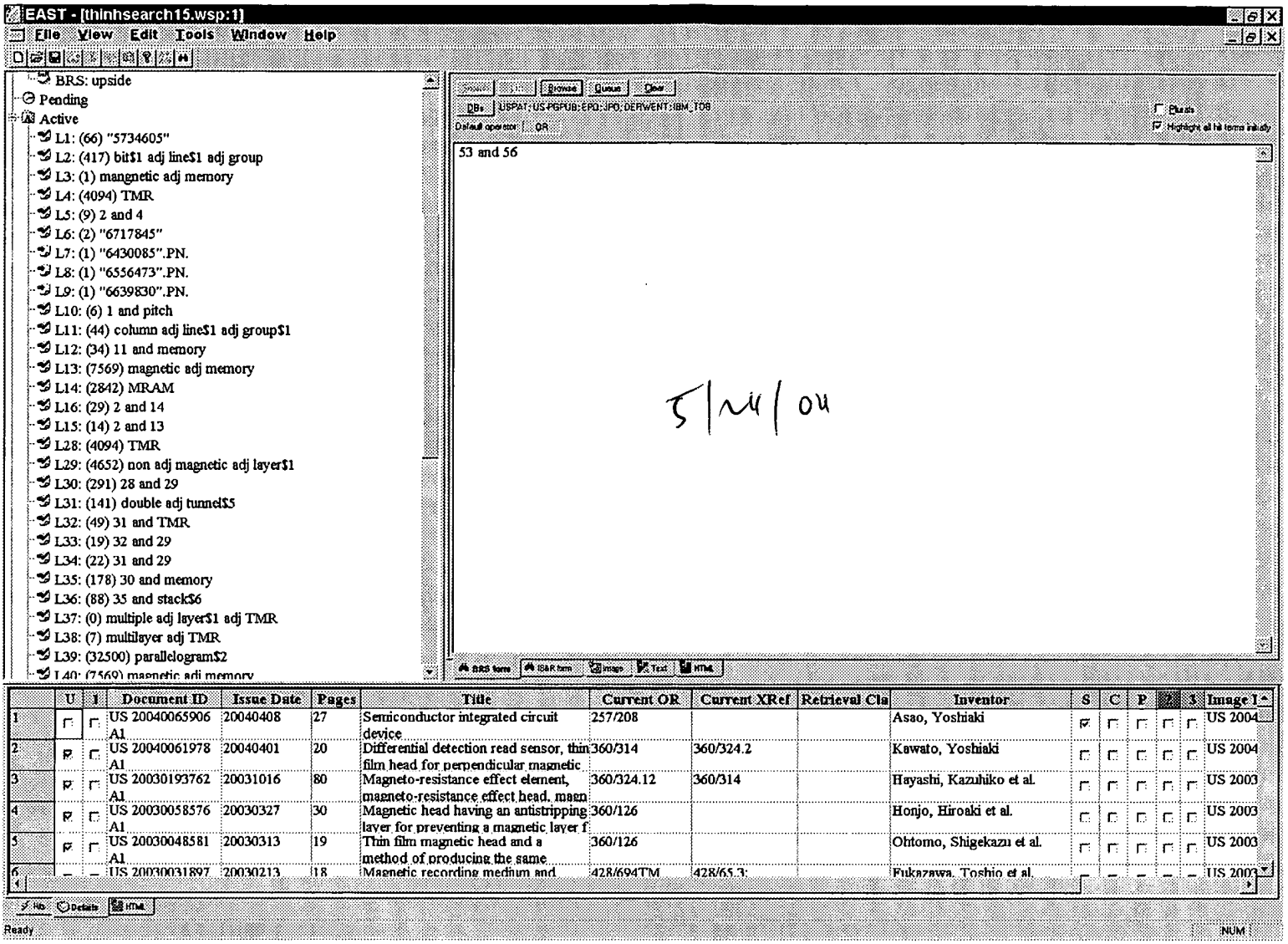

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1	☐	☐	US 20040065906 A1	20040408	27	Semiconductor integrated circuit device	257/208			Asao, Yoshiaki	☑	☐	☐	☐	☐	US 2004
2	☑	☐	US 20040061978 A1	20040401	20	Differential detection read sensor, thin film head for perpendicular magnetic	360/314	360/324.2		Kawato, Yoshiaki	☐	☐	☐	☐	☐	US 2004
3	☑	☐	US 20030193762 A1	20031016	80	Magneto-resistance effect element, magneto-resistance effect head, magn	360/324.12	360/314		Hayashi, Kazuhiko et al.	☐	☐	☐	☐	☐	US 2003
4	☑	☐	US 20030058576 A1	20030327	30	Magnetic head having an antistripping layer for preventing a magnetic layer f	360/126			Honjo, Hiroaki et al.	☐	☐	☐	☐	☐	US 2003
5	☑	☐	US 20030048581 A1	20030313	19	Thin film magnetic head and a method of producing the same	360/126			Ohtomo, Shigekazu et al.	☐	☐	☐	☐	☐	US 2003
6	–	–	US 20030031897	20030213	18	Magnetic recording medium and	428/694TM	428/65.3;		Fukazawa, Toshio et al.	☐	–	–	–	–	US 2003

L Number	Hits	Search Text	DB	Time stamp
1	66	"5734605"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 10:32
2	417	bit$1 adj line$1 adj group	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 10:33
3	1	mangnetic adj memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 10:33
4	4094	TMR	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 10:34
5	9	(bit$1 adj line$1 adj group) and TMR	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 11:13
6	2	"6717845"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 10:35
7	1		USPAT	2004/05/24 10:36
8	1		USPAT	2004/05/24 10:56
9	1		USPAT	2004/05/24 10:57
10	6	"5734605" and pitch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 11:28
11	44	column adj line$1 adj group$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 11:29
12	34	(column adj line$1 adj group$1) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 12:26
13	7569	magnetic adj memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 12:26
14	2842	MRAM	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 12:26

16	29	(bit$1 adj line$1 adj group) and MRAM	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 13:08
15	14	(bit$1 adj line$1 adj group) and (magnetic adj memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 12:54
28	4094	TMR	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 13:08
29	4652	non adj magnetic adj layer$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 13:09
30	291	TMR and (non adj magnetic adj layer$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 13:09
31	141	double adj tunnel$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 13:10
32	49	(double adj tunnel$5) and TMR	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 13:11
33	19	((double adj tunnel$5) and TMR) and (non adj magnetic adj layer$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 13:21
34	22	(double adj tunnel$5) and (non adj magnetic adj layer$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 13:51
35	178	(TMR and (non adj magnetic adj layer$1)) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 13:56
36	88	((TMR and (non adj magnetic adj layer$1)) and memory) and stack$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 14:33
37	0	multiple adj layer$1 adj TMR	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 14:03

38	7	multilayer adj TMR	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 14:04
39	32500	parallelogram$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 14:34
40	7569	magnetic adj memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 14:35
41	410	(magnetic adj memory) and resistive and cell$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 14:35
42	410	((magnetic adj memory) and resistive and cell$1) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 14:35
43	275725	257/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 14:36
44	60938	365/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 14:36
45	151434	438/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 14:37
46	74	(((magnetic adj memory) and resistive and cell$1) and memory) and 257/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 14:40
47	30	parallelogram$2 and (magnetic adj memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 15:09
48	7	magnetic adj fixing adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 15:14
49	1964	fixing adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 15:15

50	332	(fixing adj layer) and magnetic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 15:15
51	52	((fixing adj layer) and magnetic) and (non adj magnetic adj layer$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 15:40
52	1	stacked adj fixing adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 15:41
53	1964	fixing adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 15:42
54	25	non-magnetic adj sub-layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 15:45
55	35	non adj magnetic adj sub adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 15:46
56	4245	non adj magnetic adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 15:47
57	50	(fixing adj layer) and (non adj magnetic adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 15:47